

TOSHIBA

2SA1432

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SA1432

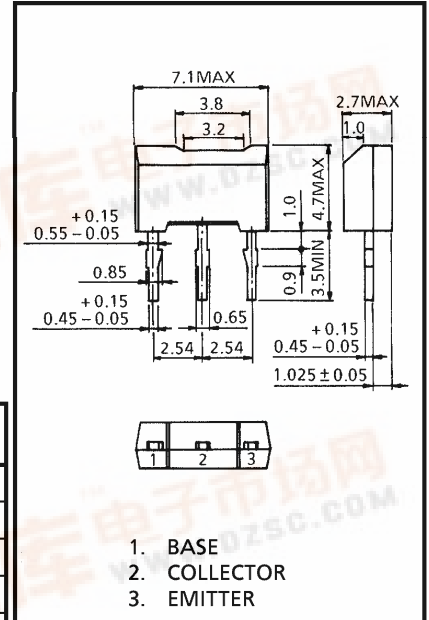
Unit in mm

HIGH VOLTAGE CONTROL APPLICATIONS
 PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS
 CATHODE RAY TUBE BRIGHTNESS CONTROL APPLICATIONS

- High Voltage : $V_{CBO} = -300\text{ V}$, $V_{CEO} = -300\text{ V}$
- Low Saturation Voltage : $V_{CE}(\text{sat}) = -0.5\text{ V (Max.)}$
- Small Collector Output Capacitance : $C_{ob} = 6\text{ pF (Typ.)}$
- Complementary to 2SC3672

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-8	V
Collector Current	I_C	-100	mA
Base Current	I_B	-20	mA
Collector Power Dissipation	P_C	1000	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



JEDEC	—
EIAJ	—
TOSHIBA	2-7D101A

Weight : 0.2 g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -300\text{ V}$, $I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -8\text{ V}$, $I_C = 0$	—	—	-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{ mA}$, $I_E = 0$	-300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}$, $I_B = 0$	-300	—	—	V
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE} = -10\text{ V}$, $I_C = -20\text{ mA}$	30	—	150	
	$h_{FE}(2)$	$V_{CE} = -10\text{ V}$, $I_C = -1\text{ mA}$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = -20\text{ mA}$, $I_B = -2\text{ mA}$	—	—	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE}(\text{sat})$	$I_C = -20\text{ mA}$, $I_B = -2\text{ mA}$	—	—	-1.2	V
Transition Frequency	f_T	$V_{CE} = -10\text{ V}$, $I_C = -20\text{ mA}$	40	60	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -20\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	—	6	8	pF

(Note) : $h_{FE}(1)$ Classification R : 30~90, O : 50~150

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